

# Jennifer K Hite

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

143  
papers

2,831  
citations

28  
h-index

46  
g-index

164  
ext. papers

3,141  
ext. citations

2.6  
avg, IF

4.82  
L-index

#	Paper	IF	Citations
143	Characterization of $\text{AlGa}_2\text{O}_3$ homoepitaxial films and MOSFETs grown by MOCVD at high growth rates. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 034005	3	15
142	Effect of GaN Substrate Properties on Vertical GaN PiN Diode Electrical Performance. <i>Journal of Electronic Materials</i> , <b>2021</b> , 50, 3013-3021	1.9	4
141	Process Optimization for Selective Area Doping of GaN by Ion Implantation. <i>Journal of Electronic Materials</i> , <b>2021</b> , 50, 4642-4649	1.9	1
140	Thermal conductivity measurements of sub-surface buried substrates by steady-state thermoreflectance. <i>Review of Scientific Instruments</i> , <b>2021</b> , 92, 064906	1.7	5
139	Site control of quantum emitters in gallium nitride by polarity. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 021103	3.4	4
138	Homoepitaxial GaN micropillar array by plasma-free photo-enhanced metal-assisted chemical etching. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2021</b> , 39, 053212	2.9	4
137	Assessment of the (010) $\text{AlGa}_2\text{O}_3$ surface and substrate specification. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2021</b> , 39, 013408	2.9	2
136	Exploiting Phonon-Resonant Near-Field Interaction for the Nanoscale Investigation of Extended Defects. <i>Advanced Functional Materials</i> , <b>2020</b> , 30, 1907357	15.6	4
135	(Invited) GaN Homoepitaxial Growth and Substrate-Dependent Effects for Vertical Power Devices. <i>ECS Transactions</i> , <b>2020</b> , 98, 63-67	1	3
134	Role of Capping Material and GaN Polarity on Mg Ion Implantation Activation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 1900789	1.6	2
133	Dilute Magnetic III-N Semiconductors Based on Rare Earth Doping. <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, P527-P535	2	3
132	Polarity dependent implanted p-type dopant activation in GaN. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SCCD07	1.4	8
131	Thermal atomic layer etching of crystalline GaN using sequential exposures of $\text{XeF}_2$ and $\text{BCl}_3$ . <i>Applied Physics Letters</i> , <b>2019</b> , 114, 243103	3.4	23
130	Reduced Contact Resistance in GaN Using Selective Area Si Ion Implantation. <i>IEEE Transactions on Semiconductor Manufacturing</i> , <b>2019</b> , 32, 478-482	2.6	2
129	Vertical power devices enabled by bulk GaN substrates <b>2019</b> ,		1
128	Defect Characterization of Multicycle Rapid Thermal Annealing Processed p-GaN for Vertical Power Devices. <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, P70-P76	2	6
127	Long range, non-destructive characterization of GaN substrates for power devices. <i>Journal of Crystal Growth</i> , <b>2019</b> , 506, 178-184	1.6	14

126	Influence of HVPE substrates on homoepitaxy of GaN grown by MOCVD. <i>Journal of Crystal Growth</i> , <b>2018</b> , 498, 352-356	1.6	14
125	Frontiers in Electronics and Photonics. <i>Electrochemical Society Interface</i> , <b>2018</b> , 27, 41-41	3.6	5
124	GaN Power Devices [Current Status and Future Directions. <i>Electrochemical Society Interface</i> , <b>2018</b> , 27, 43-47	3.6	5
123	Electrochemically Prepared Polycrystalline Copper Surface for the Growth of Hexagonal Boron Nitride. <i>Crystal Growth and Design</i> , <b>2017</b> , 17, 1669-1678	3.5	9
122	Ultra-Wide Bandgap Materials and Device. <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, Y1-Y1	2	5
121	Plasma-assisted atomic layer epitaxial growth of aluminum nitride studied with real time grazing angle small angle x-ray scattering. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2017</b> , 35, 031508	2.9	14
120	Effect of Surface Morphology on Diode Performance in Vertical GaN Schottky Diodes. <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, S3103-S3105	2	7
119	(Invited) Novel Implantation Processing and Characterization for Scalable GaN Power Devices. <i>ECS Transactions</i> , <b>2017</b> , 80, 251-260	1	
118	Electrothermal evaluation of thick GaN epitaxial layers and AlGa <sub>N</sub> /Ga <sub>N</sub> high-electron-mobility transistors on large-area engineered substrates. <i>Applied Physics Express</i> , <b>2017</b> , 10, 126501	2.4	10
117	Nanocrystalline Diamond Integration with III-Nitride HEMTs. <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, Q3036-Q3039	2	30
116	(Invited) Electrothermal Performance Optimization of III-Nitride HEMTs Capped with Nanocrystalline Diamond. <i>ECS Transactions</i> , <b>2016</b> , 72, 3-8	1	1
115	Nanocrystalline diamond capped AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistors via a sacrificial gate process. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 893-897	1.6	17
114	Selective p-type Doping of GaN:Si by Mg Ion Implantation and Multicycle Rapid Thermal Annealing. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, P124-P127	2	32
113	Atomic layer epitaxy for quantum well nitride-based devices <b>2016</b> ,		1
112	Structural, Optical, and Electrical Characterization of Monoclinic [Ga <sub>2</sub> O <sub>3</sub> Grown by MOVPE on Sapphire Substrates. <i>Journal of Electronic Materials</i> , <b>2016</b> , 45, 2031-2037	1.9	92
111	Effect of Reduced Extended Defect Density in MOCVD Grown AlGa <sub>N</sub> /Ga <sub>N</sub> HEMTs on Native Ga <sub>N</sub> Substrates. <i>IEEE Electron Device Letters</i> , <b>2016</b> , 37, 28-30	4.4	38
110	Dense nanocrystalline yttrium iron garnet films formed at room temperature by aerosol deposition. <i>Materials Research Bulletin</i> , <b>2016</b> , 76, 365-369	5.1	16
109	EditorsTChoiceOn the Radiation Tolerance of AlGa <sub>N</sub> /Ga <sub>N</sub> HEMTs. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, Q208-Q212	2	50

108	Frequency conversion in free-standing periodically oriented gallium nitride <b>2016</b> ,		3
107	Improvements in the Annealing of Mg Ion Implanted GaN and Related Devices. <i>IEEE Transactions on Semiconductor Manufacturing</i> , <b>2016</b> , 29, 343-348	2.6	23
106	Elevated temperature performance of Si-implanted solar-blind $\beta$ -Ga <sub>2</sub> O <sub>3</sub> photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2016</b> , 34, 041207	1.3	20
105	Effect of 5 MeV proton irradiation damage on performance of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2016</b> , 34, 041213	1.3	47
104	Improved Vertical GaN Schottky Diodes with Ion Implanted Junction Termination Extension. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, Q176-Q178	2	26
103	Progress in periodically oriented III-nitride materials. <i>Journal of Crystal Growth</i> , <b>2016</b> , 456, 133-136	1.6	8
102	Growth and spectroscopic characterization of monolayer and few-layer hexagonal boron nitride on metal substrates. <i>Nanoscale</i> , <b>2015</b> , 7, 3694-702	7.7	23
101	Electron backscatter diffraction study of hexagonal boron nitride growth on Cu single-crystal substrates. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 15200-5	9.5	11
100	Growth and characterization of III-N ternary thin films by plasma assisted atomic layer epitaxy at low temperatures. <i>Thin Solid Films</i> , <b>2015</b> , 589, 47-51	2.2	27
99	Determination of GaN polarity on periodically oriented surfaces. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2015</b> , 33, 011206	1.3	7
98	Symmetric Multicycle Rapid Thermal Annealing: Enhanced Activation of Implanted Dopants in GaN. <i>ECS Journal of Solid State Science and Technology</i> , <b>2015</b> , 4, P382-P386	2	32
97	Challenges to graphene growth on SiC(0 0 0 1?): Substrate effects, hydrogen etching and growth ambient. <i>Carbon</i> , <b>2015</b> , 81, 73-82	10.4	11
96	Effect of GaN surface treatment on Al <sub>2</sub> O <sub>3</sub> /n-GaN MOS capacitors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2015</b> , 33, 061201	1.3	22
95	(Invited) Vertical GaN p-i-n Diodes Formed by Mg Ion Implantation. <i>ECS Transactions</i> , <b>2015</b> , 69, 99-103	1	4
94	(Invited) Failure Mechanisms in AlGa <sub>N</sub> /Ga <sub>N</sub> HEMTs Irradiated with 2MeV Protons. <i>ECS Transactions</i> , <b>2015</b> , 66, 15-20	1	3
93	Development of solar-blind photodetectors based on Si-implanted $\beta$ -Ga <sub>2</sub> O <sub>3</sub> . <i>Optics Express</i> , <b>2015</b> , 23, 28300-5	3.3	76
92	Thermal etching of nanocrystalline diamond films. <i>Diamond and Related Materials</i> , <b>2015</b> , 59, 116-121	3.5	8
91	Selective switching of GaN polarity on Ga-polar GaN using atomic layer deposited Al <sub>2</sub> O <sub>3</sub> . <i>Applied Physics Express</i> , <b>2014</b> , 7, 025502	2.4	11

90	Advances in Diamond Integration for Thermal Management in GaN Power HEMTs. <i>ECS Transactions</i> , <b>2014</b> , 64, 185-190	1	14
89	III-nitride nanowire based light emitting diodes on carbon paper. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 442-445		1
88	Role of growth parameters in equalizing simultaneous growth of N- and Ga-polar GaN by MOCVD. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 458-461		5
87	All-epitaxial fabrication of a nanowire plasmon laser structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 754-757		
86	Comparison of the physical, chemical and electrical properties of ALD Al <sub>2</sub> O <sub>3</sub> on c- and m- plane GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 898-901		4
85	Multicycle rapid thermal annealing optimization of Mg-implanted GaN: Evolution of surface, optical, and structural properties. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 063502	2.5	28
84	Substrate-Dependent Effects on the Response of AlGaIn/GaN HEMTs to 2-MeV Proton Irradiation. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 826-828	4.4	65
83	Chemical etching behaviors of semipolar (11 22) and nonpolar (11 20) gallium nitride films. <i>Physical Chemistry Chemical Physics</i> , <b>2014</b> , 16, 15780-3	3.6	17
82	Achieving clean epitaxial graphene surfaces suitable for device applications by improved lithographic process. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 224102	3.4	25
81	Comparison of AlN encapsulants for high-temperature GaN annealing. <i>Applied Physics Express</i> , <b>2014</b> , 7, 121003	2.4	10
80	Correlation of threading screw dislocation density to GaN 2-DEG mobility. <i>Electronics Letters</i> , <b>2014</b> , 50, 1722-1724	1.1	11
79	Activation of Mg implanted in GaN by multicycle rapid thermal annealing. <i>Electronics Letters</i> , <b>2014</b> , 50, 197-198	1.1	65
78	Degradation mechanisms of AlGaIn/GaN HEMTs on sapphire, Si, and SiC substrates under proton irradiation <b>2014</b> ,		6
77	Broadband measurements of the refractive indices of bulk Gallium Nitride. <i>Optical Materials Express</i> , <b>2014</b> , 4, 1287	2.6	15
76	Impact of surface treatments on high- $\epsilon$ dielectric integration with Ga-polar and N-polar GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 03D106	1.3	17
75	Insulating gallium oxide layer produced by thermal oxidation of gallium-polar GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 565-568		11
74	(Invited) Nanocrystalline Diamond for Near Junction Heat Spreading in GaN Power HEMTs. <i>ECS Transactions</i> , <b>2014</b> , 61, 45-49	1	8
73	Topside Nanocrystalline Diamond Integration on AlGaIn/GaN HEMTs for High Temperature Operation. <i>Additional Conferences (Device Packaging HiTEC HiTEN &amp; CICMT)</i> , <b>2014</b> , 2014, 1-6	0.1	1

72	Perspectives on future directions in III-N semiconductor research. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2013</b> , 31, 058501	2.9	33
71	Nanocrystalline Diamond for near Junction Heat Spreading in GaN Power HEMTs <b>2013</b> ,		6
70	Epitaxial Growth of Cubic and Hexagonal InN Thin Films via Plasma-Assisted Atomic Layer Epitaxy. <i>Crystal Growth and Design</i> , <b>2013</b> , 13, 1485-1490	3.5	40
69	Nanocrystalline Diamond-Gated AlGaIn/GaN HEMT. <i>IEEE Electron Device Letters</i> , <b>2013</b> , 34, 1382-1384	4.4	13
68	GaN-based ultraviolet light-emitting diodes with AuClE-doped graphene electrodes. <i>Optics Express</i> , <b>2013</b> , 21, 29025-30	3.3	34
67	Nickel Foam as a Substrate for III-nitride Nanowire Growth. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1538, 311-316		
66	Reliability of GaN HEMTs: Electrical and Radiation-Induced Failure Mechanism. <i>ECS Transactions</i> , <b>2013</b> , 58, 221-225	1	3
65	GaN Power Transistors with Integrated Thermal Management. <i>ECS Transactions</i> , <b>2013</b> , 58, 279-286	1	3
64	Epitaxial growth of AlN films via plasma-assisted atomic layer epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 082110	3.4	41
63	Buried graphene electrodes on GaN-based ultra-violet light-emitting diodes. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 031108	3.4	25
62	Multicycle rapid thermal annealing technique and its application for the electrical activation of Mg implanted in GaN. <i>Journal of Crystal Growth</i> , <b>2012</b> , 350, 21-26	1.6	85
61	Improved GaN-based HEMT performance by nanocrystalline diamond capping <b>2012</b> ,		2
60	Selective chemical etch of gallium nitride by phosphoric acid. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2012</b> , 30, 040602	2.9	20
59	Development of periodically oriented gallium nitride for non-linear optics [Invited]. <i>Optical Materials Express</i> , <b>2012</b> , 2, 1203	2.6	26
58	Epitaxial graphene nucleation on C-face silicon carbide. <i>Nano Letters</i> , <b>2011</b> , 11, 1190-4	11.5	38
57	Growth of 4H- and 3C-SiC Epitaxial Layers on 4H-SiC Step-Free Mesas. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 119-122	0.4	1
56	Single n-GaN microwire/p-Silicon thin film heterojunction light-emitting diode. <i>Optics Express</i> , <b>2011</b> , 19, 21692-7	3.3	3
55	Nanostructured n-ZnO / thin film p-silicon heterojunction light-emitting diodes. <i>Optics Express</i> , <b>2011</b> , 19, 26006-10	3.3	20

54	Large-area transparent conductive few-layer graphene electrode in GaN-based ultra-violet light-emitting diodes. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 143101	3.4	84
53	GaN vertical and lateral polarity heterostructures on GaN substrates. <i>Journal of Crystal Growth</i> , <b>2011</b> , 332, 43-47	1.6	20
52	Space-charge-limited currents and trap characterization in coaxial AlGaIn/GaN nanowires. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 044303	2.5	26
51	Polarization and Space-Charge-Limited Current in III-Nitride Heterostructure Nanowires. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 3401-3406	2.9	7
50	Optical and electrical characterization of AlGaIn/GaN high electron mobility transistors irradiated with 5MeV protons. <i>Journal of Crystal Growth</i> , <b>2011</b> , 326, 62-64	1.6	14
49	Gallium nitride light emitter on a patterned sapphire substrate for improved defectivity and light extraction efficiency. <i>Current Applied Physics</i> , <b>2011</b> , 11, 682-686	2.6	7
48	Initiating polarity inversion in GaN growth using an AlN interlayer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2011</b> , 208, 1504-1506	1.6	18
47	Vertical zinc oxide nanowires embedded in self-assembled photonic crystal. <i>Photonics and Nanostructures - Fundamentals and Applications</i> , <b>2011</b> , 9, 91-94	2.6	6
46	Photo-enhanced chemical etched GaN LED on silicon substrate. <i>Journal of Crystal Growth</i> , <b>2011</b> , 326, 58-61	1.6	4
45	Wet etching of non-polar gallium nitride light-emitting diode structure for enhanced light extraction. <i>Journal of Crystal Growth</i> , <b>2011</b> , 326, 65-68	1.6	11
44	Electrical and optical characterization of GaN micro-wires. <i>Journal of Crystal Growth</i> , <b>2011</b> , 326, 81-84	1.6	1
43	Emission enhancement from nonpolar a-plane III-nitride nanopillar. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2011</b> , 29, 021004	1.3	3
42	Epitaxial graphene surface preparation for atomic layer deposition of Al <sub>2</sub> O <sub>3</sub> . <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 124304	2.5	37
41	Observations on C-Face SiC Graphene Growth in Argon. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 789-792	0.4	2
40	Assessment of GaN Surface Pretreatment for Atomic Layer Deposited High-k Dielectrics. <i>Applied Physics Express</i> , <b>2011</b> , 4, 055802	2.4	65
39	Development of Enhancement Mode AlN/Ultrathin AlGaIn/GaN HEMTs by Selective Wet Etching. <i>ECS Transactions</i> , <b>2010</b> , 28, 65-70	1	
38	Effect of Temperature and Al Concentration on the Electrical Performance of GaN and Al <sub>0.2</sub> Ga <sub>0.8</sub> N Accumulation-Mode FET Devices. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 1215-1218	0.4	
37	Quasi-Ballistic Hole Transport in an AlGaIn/GaN Nanowire. <i>ECS Transactions</i> , <b>2010</b> , 28, 47-52	1	2



36	Techniques for the Dry Transfer of Epitaxial Graphene onto Arbitrary Substrates. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 633-636	0.4	1
35	Dry Techniques for Epitaxial Graphene Transfer. <i>Materials Research Society Symposia Proceedings</i> , <b>2010</b> , 1259, 1		1
34	Reverse gate bias-induced degradation of AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2010</b> , 28, 1044-1047	1.3	19
33	Violet electroluminescence from p-Ga <sub>N</sub> thin film/n-Ga <sub>N</sub> nanowire homojunction. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 132105	3.4	7
32	Electroluminescence from ZnO nanoflowers/Ga <sub>N</sub> thin film p-n heterojunction. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 082111	3.4	8
31	Polarization fields in III-nitride nanowire devices. <i>Nanotechnology</i> , <b>2010</b> , 21, 145205	3.4	22
30	Quantum linear magnetoresistance in multilayer epitaxial graphene. <i>Nano Letters</i> , <b>2010</b> , 10, 3962-5	11.5	181
29	Photopolymerization of self-assembled monolayers of diacetylenic alkylphosphonic acids on group-III nitride substrates. <i>Langmuir</i> , <b>2010</b> , 26, 10725-30	4	17
28	Technique for the dry transfer of epitaxial graphene onto arbitrary substrates. <i>ACS Nano</i> , <b>2010</b> , 4, 1108-1117	14.7	163
27	Transparent conductive graphene electrode in Ga <sub>N</sub> -based ultra-violet light emitting diodes. <i>Optics Express</i> , <b>2010</b> , 18, 23030-4	3.3	36
26	Ga <sub>N</sub> single crystals of different habit grown from solution at near atmospheric pressure. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 2551-2557	1.6	6
25	Morphology characterization of argon-mediated epitaxial graphene on C-face SiC. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 222103	3.4	75
24	Approach for dislocation free Ga <sub>N</sub> epitaxy. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 3143-3146	1.6	12
23	Characterization of Recessed-Gate AlGa <sub>N</sub> /Ga <sub>N</sub> HEMTs as a Function of Etch Depth. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 478-481	1.9	16
22	Electrical and Optical Characterization of AlGa <sub>N</sub> /Ga <sub>N</sub> HEMTs with In Situ and Ex Situ Deposited Si <sub>N</sub> x Layers. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 2452-2458	1.9	22
21	Array of Two UV-Wavelength Detector Types. <i>IEEE Transactions on Electron Devices</i> , <b>2010</b> , 57, 1224-1229	2.9	11
20	Electrical and structural characterizations of non-polar AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructures. <i>Thin Solid Films</i> , <b>2010</b> , 518, 1747-1750	2.2	9
19	Post-annealing behavior of Ni/Au Schottky contact on non-polar a-plane Ga <sub>N</sub> . <i>Thin Solid Films</i> , <b>2010</b> , 518, 5810-5812	2.2	8



18	Controlled fabrication of gallium nitride nano- and micro-wires by dielectrophoretic force and torque. <i>Current Applied Physics</i> , <b>2010</b> , 10, 703-707	2.6	2
17	Nitrogen-polar gallium nitride substrates as solid-state pH-selective potentiometric sensors. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 142501	3.4	4
16	Enhancement of light extraction efficiency of ultraviolet light emitting diodes by patterning of SiO <sub>2</sub> nanosphere arrays. <i>Thin Solid Films</i> , <b>2009</b> , 517, 2742-2744	2.2	23
15	Towards a polariton-based light emitter based on non-polar GaN quantum wells. <i>Solid State Communications</i> , <b>2009</b> , 149, 2039-2042	1.6	6
14	Nature of luminescence and strain in gallium nitride nanowires. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2982-2986	1.6	5
13	An AlN/Ultrathin AlGa <sub>N</sub> /Ga <sub>N</sub> HEMT Structure for Enhancement-Mode Operation Using Selective Etching. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 1251-1253	4.4	24
12	Effects of proton irradiation on the magnetic properties of GaGdN and GaCrN. <i>New Journal of Physics</i> , <b>2008</b> , 10, 055005	2.9	7
11	Inductively coupled plasma etching of nano-patterned sapphire for flip-chip GaN light emitting diode applications. <i>Thin Solid Films</i> , <b>2008</b> , 516, 7744-7747	2.2	19
10	Characterization of erbium chloride seeded gallium nitride nanocrystals. <i>Thin Solid Films</i> , <b>2008</b> , 517, 1111-1114	2.1	11
9	Effect of Si Co Doping on Ferromagnetic Properties of GaGdN. <i>Journal of Electronic Materials</i> , <b>2007</b> , 36, 391-396	1.9	25
8	Optical and magnetic behavior of erbium-doped GaN epilayers grown by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 054106	3.4	27
7	Ferromagnetic Properties of GaGdN Co-Doped with Si. <i>ECS Transactions</i> , <b>2006</b> , 3, 409-414	1	
6	Magnetic and Optical Properties of Eu-doped GaN. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 955, 1		
5	Optical and magnetic properties of Eu-doped GaN. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 132119	3.4	69
4	Effect of Gd implantation on the structural and magnetic properties of GaN and AlN. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 042102	3.4	59
3	Effect of growth conditions on the magnetic characteristics of GaGdN. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 092119	3.4	26
2	Ultraviolet photoluminescence from Gd-implanted AlN epilayers. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 152107	3.4	43
1	Role of growth conditions on magnetic properties of AlCrN grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 052101	3.4	60

